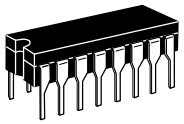
MC14502B

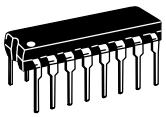
Strobed Hex Inverter/Buffer

The MC14502B is a strobed hex buffer/inverter with 3–state outputs, an inhibit control, and guaranteed TTL drive over the temperature range. The 3–state output simplifies design by allowing a common bus.

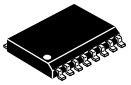
- Separate Output Disable Control
- 3–State Output
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving 4LSTTL Loads Over the Rated Temperature Range



L SUFFIX
CERAMIC
CASE 620



P SUFFIX
PLASTIC
CASE 648



DW SUFFIX
SOIC
CASE 751G

ORDERING INFORMATION

MC14XXXBCP	Plastic
MC14XXXBCL	Ceramic
MC14XXXBDW	SOIC

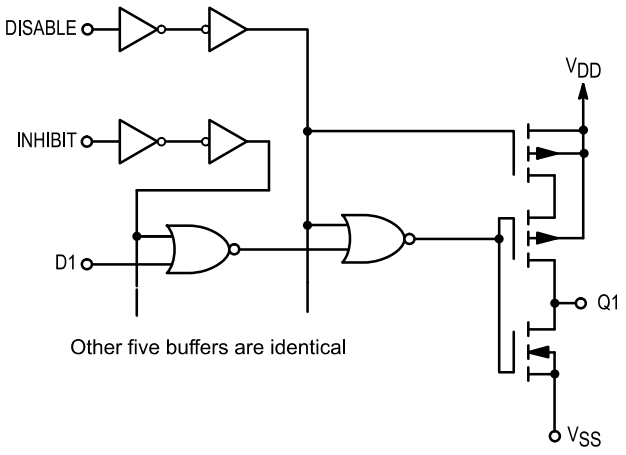
T_A = – 55° to 125°C for all packages.

MAXIMUM RATINGS* (Voltages Referenced to V_{SS})

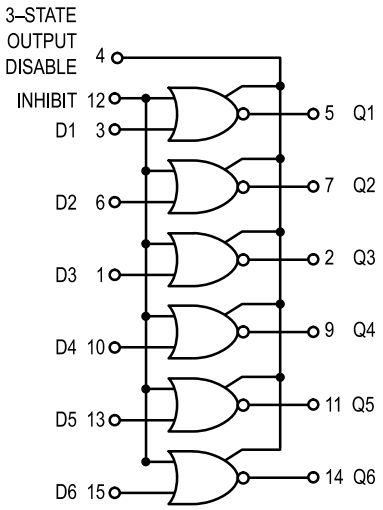
Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage	– 0.5 to + 18.0	V
V_{in}, V_{out}	Input or Output Voltage (DC or Transient)	– 0.5 to V_{DD} + 0.5	V
I_{in}	Input Current (DC or Transient), per Pin	± 10	mA
I_{out}	Output Current (DC or Transient), per Pin	+ 30	mA
P_D	Power Dissipation, per Package†	500	mW
T_{stg}	Storage Temperature	– 65 to + 150	°C
T_L	Lead Temperature (8–Second Soldering)	260	°C

* Maximum Ratings are those values beyond which damage to the device may occur.
†Temperature Derating:
Plastic "P and D/DW" Packages: – 7.0 mW/°C From 65°C To 125°C
Ceramic "L" Packages: – 12 mW/°C From 100°C To 125°C

CIRCUIT DIAGRAM



LOGIC DIAGRAM



TRUTH TABLE

D_n	Inhibit	Disable	Q_n
0	0	0	1
1	0	0	0
X	1	0	0
X	X	1	High Impedance

X = Don't Care

REV 3
1/94

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	– 55°C Min	– 55°C Max	25°C Min	25°C Typ #	25°C Max	125°C Min	125°C Max	Unit
Output Voltage "0" Level V_{in} = V_{DD} or 0	V_{OL}	5.0 10 15	— — —	0.05 0.05 0.05	— — —	0 0 0	0.05 0.05 0.05	— — —	0.05 0.05 0.05	Vdc
"1" Level V_{in} = 0 or V_{DD}	V_{OH}	5.0 10 15	4.95 9.95 14.95	— — —	4.95 9.95 14.95	5.0 10 15	— — —	4.95 9.95 14.95	— — —	Vdc
Input Voltage "0" Level (V_O = 4.5 or 0.5 Vdc) (V_O = 9.0 or 1.0 Vdc) (V_O = 13.5 or 1.5 Vdc)	V_{IL}	5.0 10 15	— — —	1.5 3.0 4.0	— — —	2.25 4.50 6.75	1.5 3.0 4.0	— — —	1.5 3.0 4.0	Vdc
"1" Level (V_O = 0.5 or 4.5 Vdc) (V_O = 1.0 or 9.0 Vdc) (V_O = 1.5 or 13.5 Vdc)	V_{IH}	5.0 10 15	3.5 7.0 11	— — —	3.5 7.0 11	2.75 5.50 8.25	— — —	3.5 7.0 11	— — —	Vdc
Output Drive Current (V_{OH} = 2.5 Vdc) Source (V_{OH} = 4.6 Vdc) (V_{OH} = 9.5 Vdc) (V_{OH} = 13.5 Vdc)	I_{OH}	5.0 5.0 10 15	– 3.0 – 0.64 – 1.6 – 4.2	— — — —	– 2.4 – 0.51 – 1.3 – 3.4	– 4.2 – 0.88 – 2.25 – 8.8	— — — —	– 1.7 – 0.36 – 0.9 – 2.4	— — — —	mAdc
(V_{OL} = 0.4 Vdc) Sink (V_{OL} = 0.5 Vdc) (V_{OL} = 1.5 Vdc)	I_{OL}	5.0 10 15	3.5 7.8 29	— — —	2.8 6.3 24	6.6 17 66	— — —	2.0 4.4 16	— — —	mAdc
Input Current	I_{in}	15	—	± 0.1	—	±0.00001	± 0.1	—	± 1.0	µAdc
Input Capacitance (V_{in} = 0)	C_{in}	—	—	—	—	5.0	7.5	—	—	pF
Quiescent Current (Per Package)	I_{DD}	5.0 10 15	— — —	1.0 2.0 4.0	— — —	0.002 0.004 0.006	1.0 2.0 4.0	— — —	30 60 120	µAdc
Total Supply Current**† (Dynamic plus Quiescent, Per Package) (C_L = 50 pF on all outputs, all buffers switching)	I_T	5.0 10 15	I_T = (2.7 µA/kHz) f + I_{DD} I_T = (5.3 µA/kHz) f + I_{DD} I_T = (8.0 µA/kHz) f + I_{DD}							µAdc
Three–State Leakage Current	I_{TL}	15	—	± 0.1	—	± 0.0001	± 0.1	—	± 3.0	µAdc

#Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

** The formulas given are for the typical characteristics only at 25°C.

†To calculate total supply current at loads other than 50 pF:

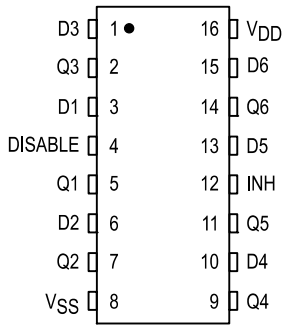
$$I_T(C_L) = I_T(50\ pF) + (C_L - 50)\ Vfk$$

where: I_T is in µA (per package), C_L in pF, V = (V_{DD} – V_{SS}) in volts, f in kHz is input frequency, and k = 0.006.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

PIN ASSIGNMENT



SWITCHING CHARACTERISTICS* (C_L = 50 pF, T_A = 25°C)

Characteristic	Symbol	V_{DD}	All Types			Unit
			Min	Typ #	Max	
Output Rise Time	t_{TLH}	5.0 10 15	— — —	100 50 40	200 100 80	ns
Output Fall Time	t_{THL}	5.0 10 15	— — —	40 20 15	80 40 30	ns
Propagation Delay Time Data to Q	t_{PHL}	5.0 10 15	— — —	135 55 40	270 110 80	ns
Propagation Delay Time, Inhibit to Q	t_{PHL}	5.0 10 15	— — —	335 145 95	670 290 190	ns
Propagation Delay Time Data to Q, Inhibit to Q	t_{PLH}	5.0 10 15	— — —	295 130 95	590 260 190	ns
3–State Propagation Delay, Output “1” to High Impedance	t_{PHZ}	5.0 10 15	— — —	65 30 25	130 60 50	ns
3–State Propagation Delay, High Impedance to “1” Level	t_{PZH}	5.0 10 15	— — —	260 105 80	520 210 160	ns
3–State Propagation Delay, Output “0” to High Impedance	t_{PLZ}	5.0 10 15	— — —	150 70 55	300 140 110	ns
3–State Propagation Delay, High Impedance to “0” Level	t_{PZL}	5.0 10 15	— — —	160 65 50	320 130 100	ns

* The formulas given are for the typical characteristics only at 25°C.
#Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.

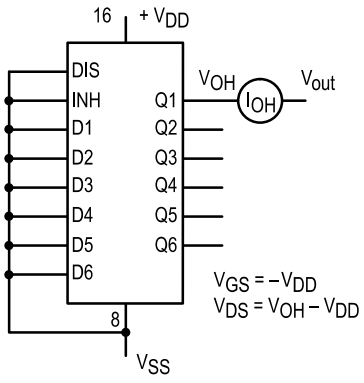


Figure 1. Typical Output Source Current Test Circuit (I_{OH})

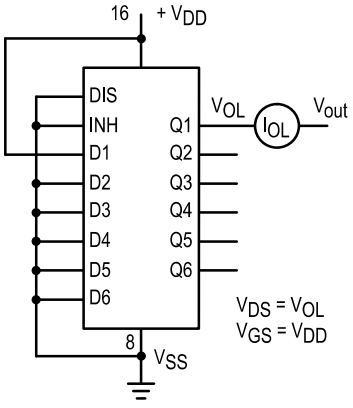


Figure 2. Typical Output Sink Current Test Circuit (I_{OL})

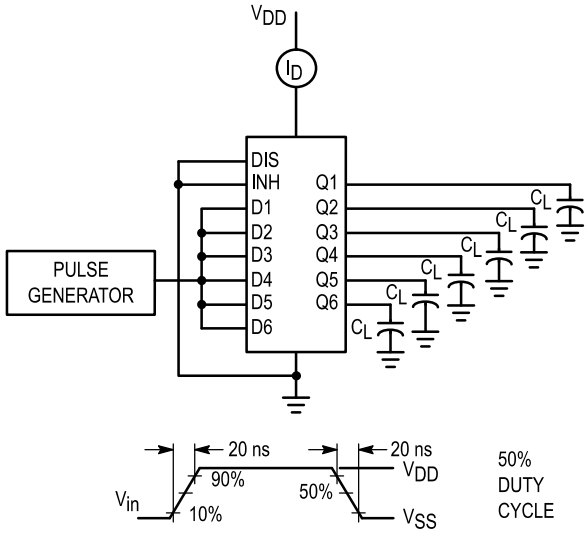
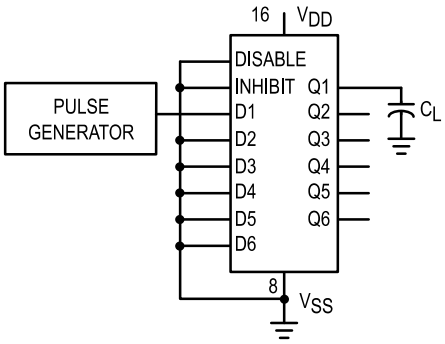


Figure 3. Power Dissipation Test Circuit and Waveform

Switch Positions for 3–State Test

Test	S1	S2	S3	S4
t_{PHZ}	Open	Closed	Closed	Open
t_{PLZ}	Closed	Open	Open	Closed
t_{PZL}	Closed	Open	Open	Closed
t_{PZH}	Open	Closed	Closed	Open



For all t_{TLH}, t_{THL}, t_{PHL}, and t_{PLH} measurements V_{in} may be applied to any other D_n input or to inhibit.

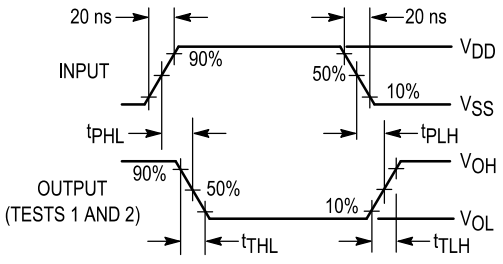
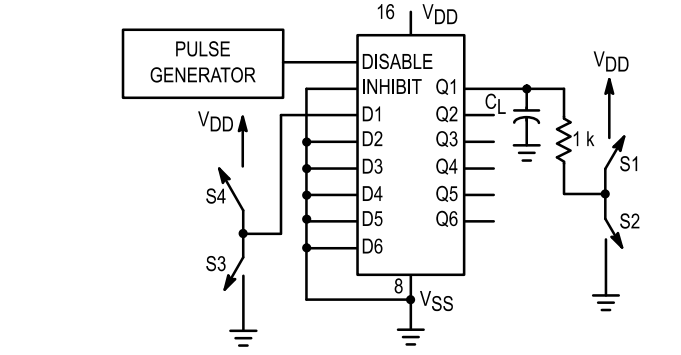


Figure 4. AC Test Circuit and Waveforms (t_{TLH}, t_{THL}, T_{PLH}, and t_{PHL})



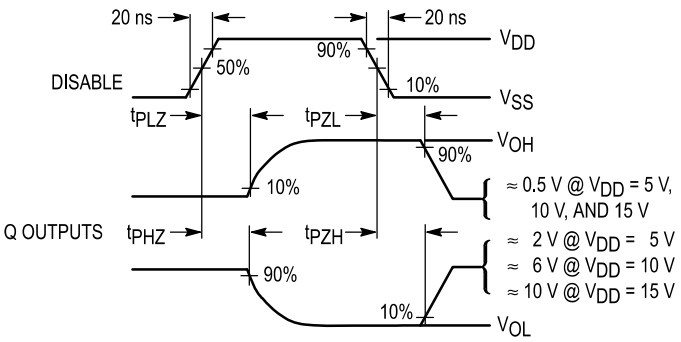
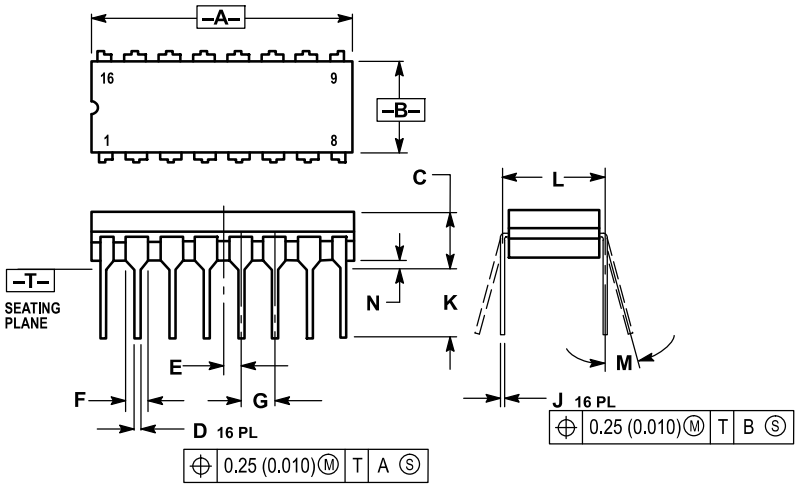


Figure 5. 3–State AC Test Circuit and Waveforms (t_{PHZ}, t_{PLZ}, t_{PZH}, t_{PZL})

OUTLINE DIMENSIONS

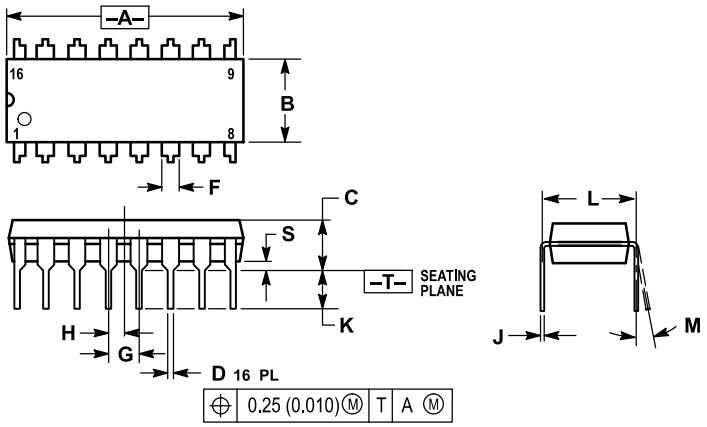
L SUFFIX
CERAMIC DIP PACKAGE
CASE 620–10
ISSUE V



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
4. DIMENSION F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC BODY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.750	0.785	19.05	19.93
B	0.240	0.295	6.10	7.49
C	—	0.200	—	5.08
D	0.015	0.020	0.39	0.50
E	0.050 BSC		1.27 BSC	
F	0.055	0.065	1.40	1.65
G	0.100 BSC		2.54 BSC	
H	0.008	0.015	0.21	0.38
K	0.125	0.170	3.18	4.31
L	0.300 BSC		7.62 BSC	
M	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01

P SUFFIX
PLASTIC DIP PACKAGE
CASE 648–08
ISSUE R



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10°	0°	10°
S	0.020	0.040	0.51	1.01